



## SSC8205GTA

### Common Drain N-Channel Enhancement Mode MOSFET

#### ➤ Features

VDS	VGS	RDSON Typ.	ID
20V	±12V	20mR@4V5	6.5A
		25mR@2V5	

#### ➤ Description

Advanced trench process technology. High density cell design for ultra-low on-resistance. High power and current handling capability. Fully characterized avalanche voltage and current.

#### ➤ Applications

- Li-ion battery protection
- Load switch
- DCDC conversion

#### ➤ Ordering Information

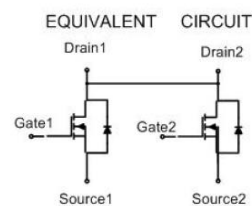
Device	Package	Shipping
SSC8205GTA	TSSOP8	3000/Reel

#### ➤ Pin configuration

Top view



TSSOP-8



PIN NUMBER	NAME	FUNCTION
1	D	DRAIN
2,3	S1	SOURCE1
4	G1	GATE1
5	G2	GATE2
6,7	S2	SOURCE2
8	D	DRAIN



Marking



➤ **Absolute Maximum Ratings**( $T_A=25^{\circ}\text{C}$  unless otherwise noted)

Symbol	Parameter	Ratings	Unit
$V_{DSS}$	Drain-to-Source Voltage	20	V
$V_{GSS}$	Gate-to-Source Voltage	$\pm 12$	V
$I_D$	Continuous Drain Current <sup>a</sup>	6.5	A
$I_{DM}$	Pulsed Drain Current <sup>b</sup>	20	A
$P_D$	Power Dissipation <sup>c</sup>	1.4	W
$P_{DSM}$	Power Dissipation <sup>a</sup>	0.9	W
$T_J$	Operation junction temperature	-55 to 150	$^{\circ}\text{C}$
$T_{STG}$	Storage temperature range	-55 to 150	$^{\circ}\text{C}$

➤ **Thermal Resistance Ratings**( $T_A=25^{\circ}\text{C}$  unless otherwise noted)

Symbol	Parameter	Typical	Maximum	Unit
$R_{\theta JA}$	Junction-to-Ambient Thermal Resistance <sup>a</sup>		145	$^{\circ}\text{C}/\text{W}$
$R_{\theta JC}$	Junction-to-Case Thermal Resistance		95	

Note:

- The value of  $R_{\theta JA}$  is measured with the device mounted on 1 in<sup>2</sup> FR-4 board with 2oz.copper,in a still air environment with  $T_A=25^{\circ}\text{C}$ .The value in any given application depends on the user is specific board design. The current rating is based on the  $t \leq 10\text{s}$  thermal resistance rating.
- Repetitive rating, pulse width limited by junction temperature.
- The power dissipation  $P_D$  is based on  $T_{J(MAX)}=150^{\circ}\text{C}$ , using junction-to-case thermal resistance, and is more useful in setting the upper dissipation limit for cases where additional heat sinking is used.



➤ **Electronics Characteristics**( $T_A=25^{\circ}\text{C}$  unless otherwise noted)

Symbol	Parameter	Test Conditions	Min	Typ.	Max	Unit
$V_{(BR)DSS}$	Drain-Source Breakdown Voltage	$V_{GS}=0V, I_D=250\mu A$	20			V
$V_{GS(th)}$	Gate Threshold Voltage	$V_{DS}=V_{GS}, I_D=250\mu A$	0.4	0.6	1	V
$R_{DS(on)}$	Drain-Source On- Resistance	$V_{GS}=4.5V, I_D=3A$		20	24	mR
		$V_{GS}=2.5V, I_D=2A$		25	30	
$I_{DSS}$	Zero Gate Voltage Drain Current	$V_{DS}=16V, V_{GS}=0V$			1	$\mu A$
$I_{GSS}$	Gate-Source leak current	$V_{GS}=\pm 12V, V_{DS}=0V$			$\pm 100$	nA
$G_{FS}$	Transconductance	$V_{DS}=5V, I_D=4.5A$		10		S
$V_{SD}$	Forward Voltage	$V_{GS}=0V, I_S=1.25A$		0.8	1.3	V
$C_{iss}$	Input Capacitance	$V_{DS}=8V, V_{GS}=0V, f=1MHz$		600		pF
$C_{oss}$	Output Capacitance			330		
$C_{rss}$	Reverse Transfer Capacitance			140		
$T_{D(ON)}$	Turn-on delay time	$V_{GEN}=4.5V,$ $V_{DS}=10V, R_G=6R, I_D=1A$		8		ns
$T_r$	Rise Time			10		
$T_{D(OFF)}$	Turn-off delay time			35		
$T_f$	Fall Time			30		
$Q_g$	Total Gate charge	$V_{GS}=4.5V, V_{DS}=10V, I_D=6A$		10		nC
$Q_{gs}$	Gate to Source charge			2.3		
$Q_{gd}$	Gate to Drain charge			2.9		

➤ **Typical Characteristics**( $T_A=25^\circ\text{C}$  unless otherwise noted)

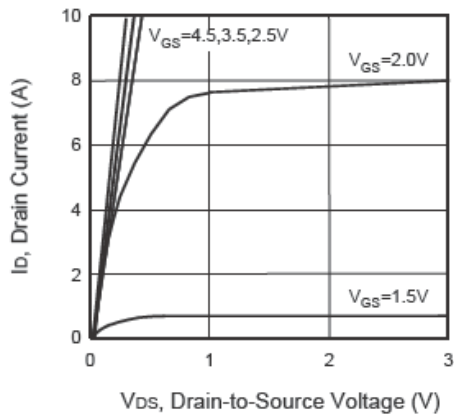


Figure 1. Output Characteristics

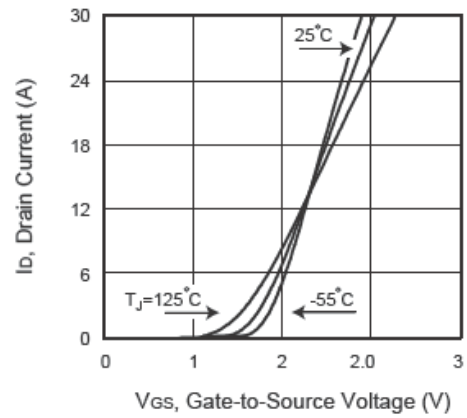


Figure 2. Transfer Characteristics

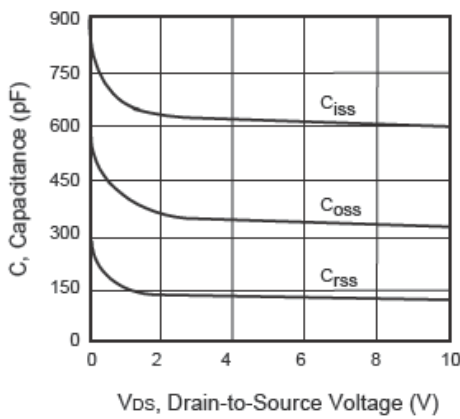


Figure 3. Capacitance

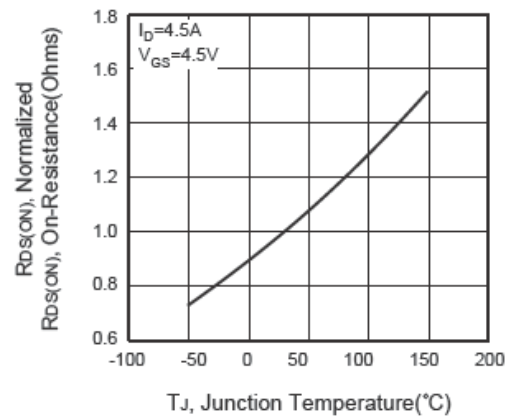


Figure 4. On-Resistance Variation with Temperature

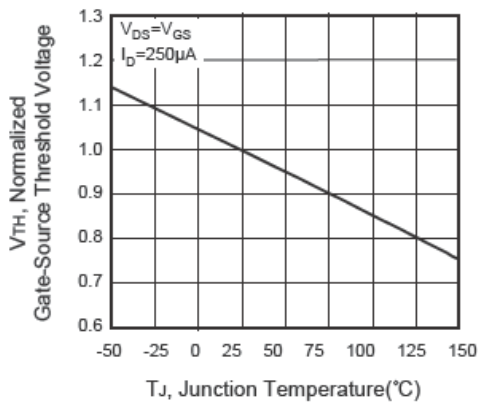


Figure 5. Gate Threshold Variation with Temperature

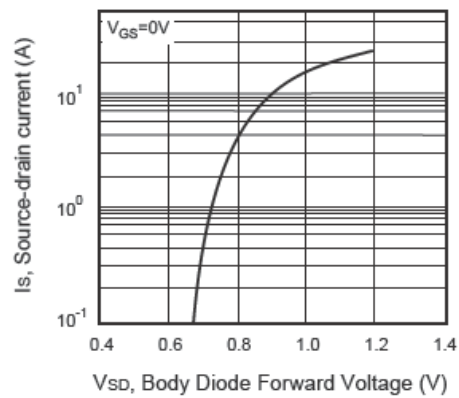


Figure 6. Body Diode Forward Voltage Variation with Source Current

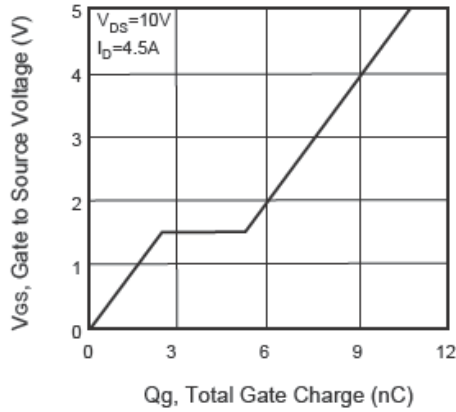


Figure 7. Gate Charge

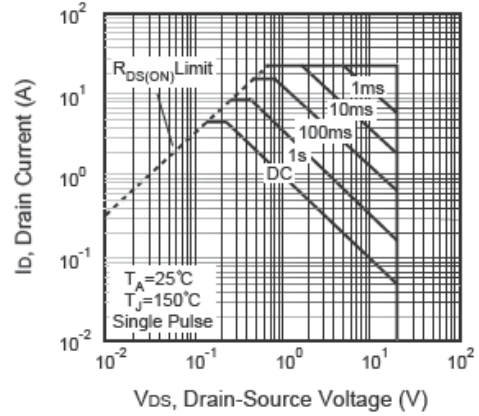


Figure 8. Maximum Safe Operating Area

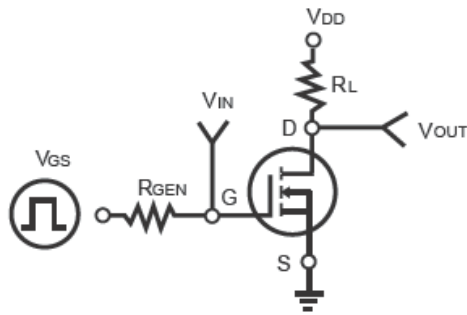


Figure 9. Switching Test Circuit

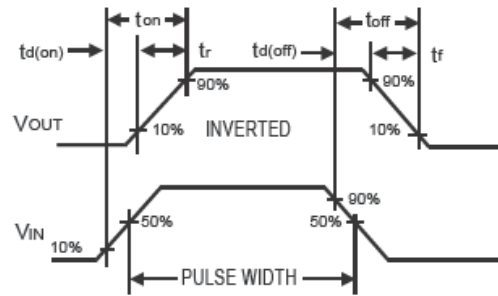


Figure 10. Switching Waveforms

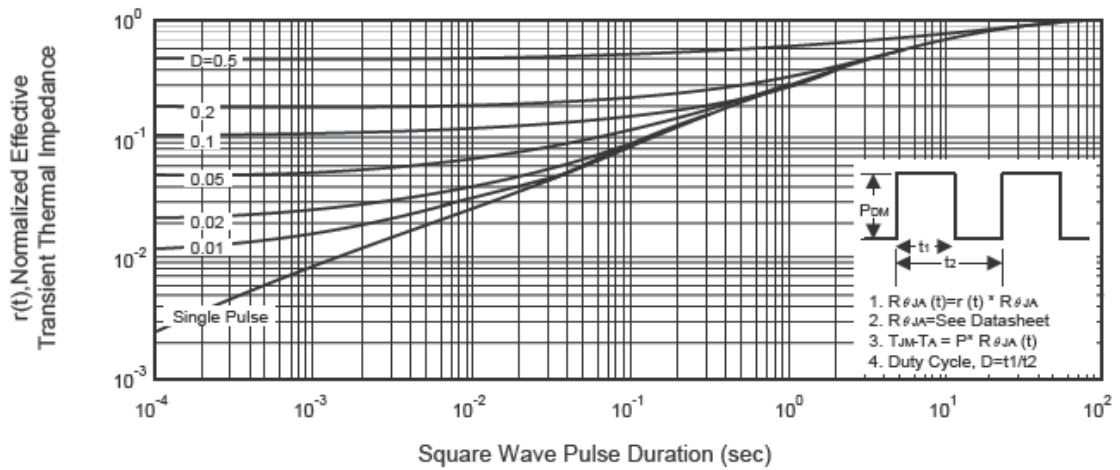
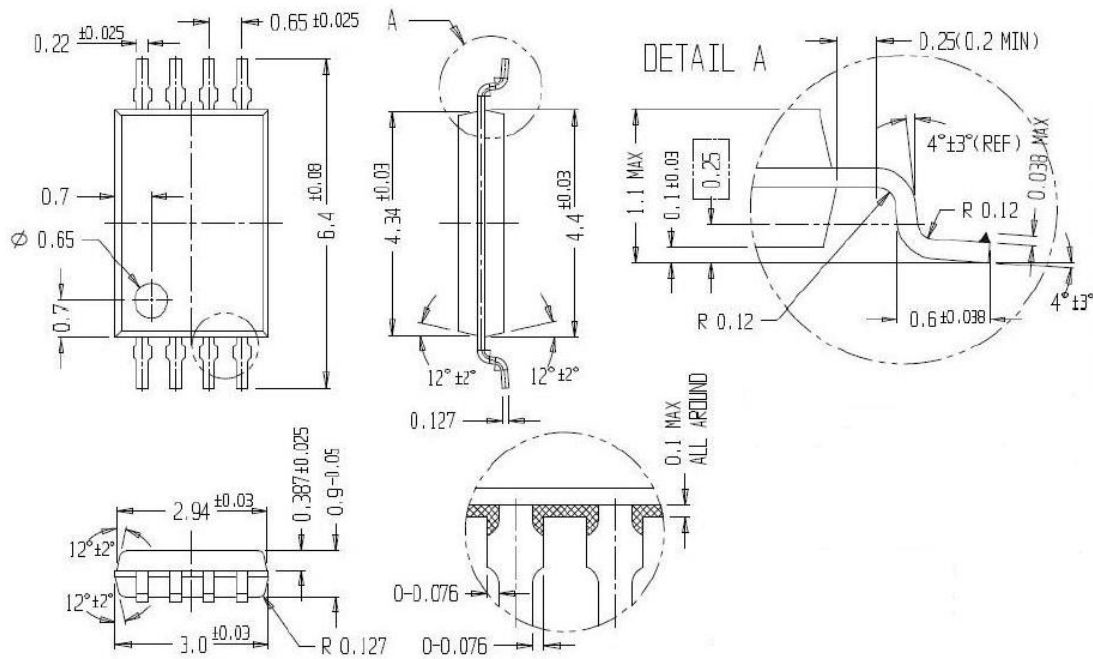


Figure 11. Normalized Thermal Transient Impedance Curve



➤ Package Information



**DISCLAIMER**

SSCSEMI RESERVES THE RIGHT TO MAKE CHANGES WITHOUT FURTHER NOTICE TO ANY PRODUCTS HEREIN TO IMPROVE RELIABILITY, FUNCTION OR DESIGN. SSCSEMI DOES NOT ASSUME ANY LIABILITY ARISING OUT OF THE APPLICATION OR USE OF ANY PRODUCT OR CIRCUIT DESCRIBED HEREIN; NEITHER DOES IT CONVEY ANY LICENCE UNDER ITS PATENT RIGHTS, NOR THE RIGHTS OF OTHERS.

THE GRAPHS PROVIDED IN THIS DOCUMENT ARE STATISTICAL SUMMARIES BASED ON A LIMITED NUMBER OF SAMPLES AND ARE PROVIDED FOR INFORMATIONAL PURPOSE ONLY. THE PERFORMANCE CHARACTERISTICS LISTED IN THEM ARE NOT TESTED OR GUARANTEED. IN SOME GRAPHS, THE DATA PRESENTED MAY BE OUTSIDE THE SPECIFIED OPERATING RANGE (E.G. OUTSIDE SPECIFIED POWER SUPPLY RANGE) AND THEREFORE OUTSIDE THE WARRANTED RANGE.

OUR PRODUCT SPECIFICATIONS ARE ONLY VALID IF OBTAINED THROUGH THE COMPANY'S OFFICIAL WEBSITE, CRM SYSTEM, OR OUR SALES PERSONNEL CHANNELS. IF CHANGES OR SPECIAL VERSIONS ARE INVOLVED, THEY MUST BE STAMPED WITH A QUALITY SEAL AND MARKED WITH A SPECIAL VERSION NUMBER TO BE VALID.